DSS5160FDB

60V DUAL PNP LOW VCE(sat) TRANSISTOR

Features

- BV_{CEO} > -60V
- I_C = -1A high Continuous Collector Current
- $R_{CE(sat)}$ = 200mΩ for a Low Equivalent On-Resistance
- Low Saturation Voltage $V_{CE(sat)}$ < 340mV @ 1A
- P_D up to 2.47W for power demanding applications
- $R_{\theta JA}$ efficient, 40% lower than SOT26
- Low profile 0.6mm high package for thin applications
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

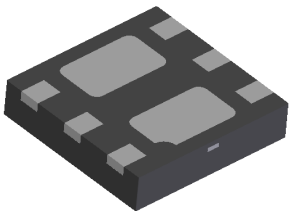
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu, Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.0065 grams (Approximate)

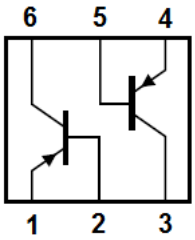
Application

- Load Switch
- Power Management
- Charging Circuits
- Power Switches (e.g. Motors, Fans)

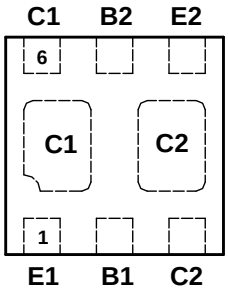
U-DFN2020-6



Bottom View



Device Symbol



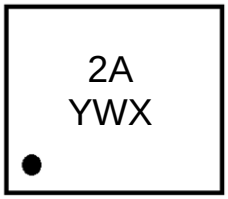
Top View
Pin-Out

Ordering Information (Notes 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS5160FDB-7	2A	7	8	3,000

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



2A = Product type Marking Code
Y = Year: 0~9
W = Week: A~Z : 1~26 week;
a~z; 27~52 week; z represents 52 and 53 week
X = A~Z: Internal code

Absolute Maximum Ratings – Q1 & Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	I_C	-1	A
Peak Pulse Collector Current	I_{CM}	-1.5	A
Base Current	I_B	-300	mA
Peak Base Current	I_{BM}	-1	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

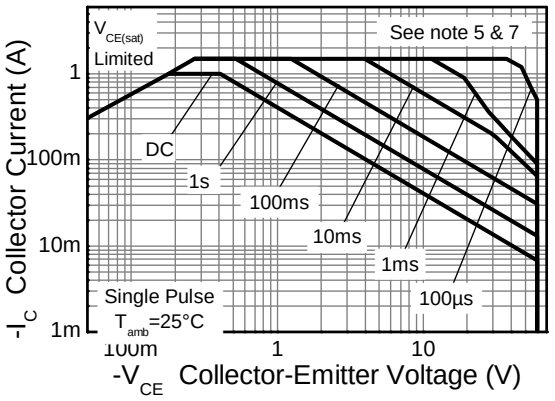
Characteristic		Symbol	Value	Unit
Power Dissipation	(Notes 5 & 7)	P_D	405	mW
	(Notes 5 & 8)		510	
	(Notes 6 & 7)		1650	
	(Notes 6 & 8)		2470	
Thermal Resistance, Junction to Ambient	(Notes 5 & 7)	$R_{\theta JA}$	308	°C/W
	(Notes 5 & 8)		245	
	(Notes 6 & 7)		76	
	(Notes 6 & 8)		51	
Thermal Resistance, Junction to Lead	(Note 9)	$R_{\theta JL}$	18	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 10)

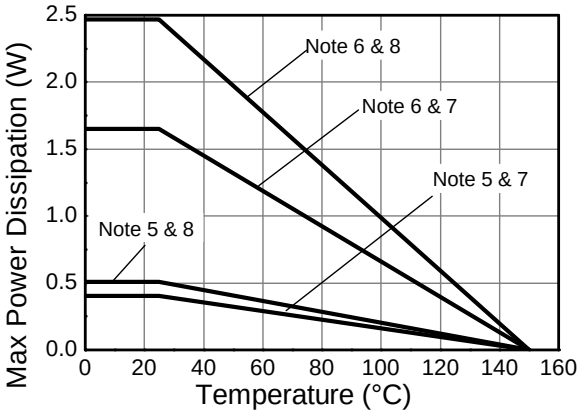
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	C

Notes:
5. For a device mounted with the exposed collector pads on minimum recommended pad layout that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
6. Same as note (5), except the device is mounted with the collector pad on 28mm x 28mm (8cm^2) 2oz copper.
7. For a dual device with one active die.
8. For dual device with 2 active die running at equal power.
9. Thermal resistance from junction to solder-point (on the exposed collector pads).
10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

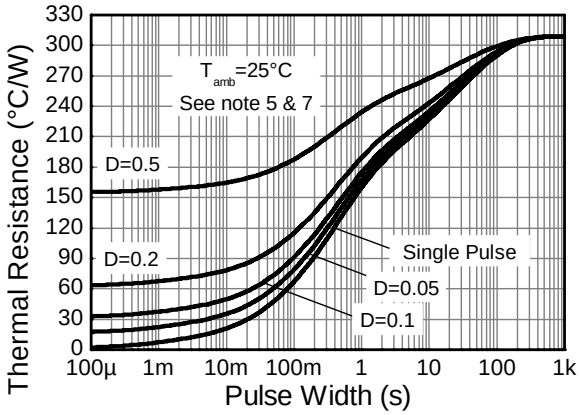
Thermal Characteristics and Derating Information



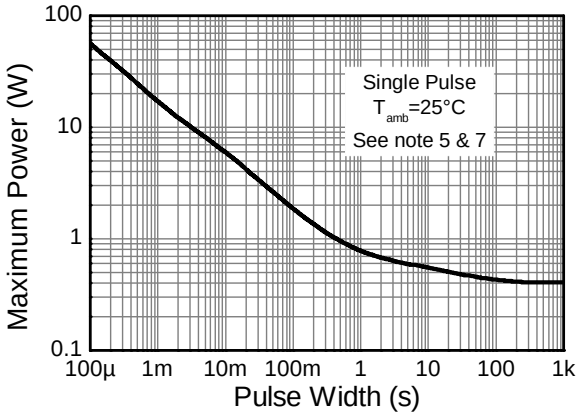
Safe Operating Area



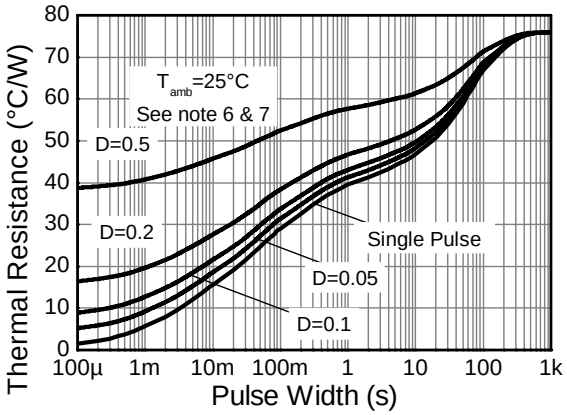
Derating Curve



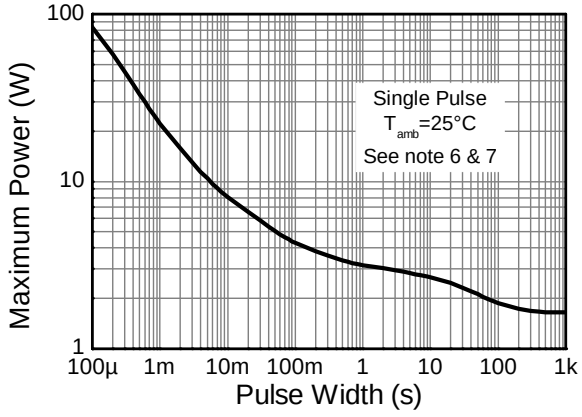
Transient Thermal Impedance



Pulse Power Dissipation



Transient Thermal Impedance



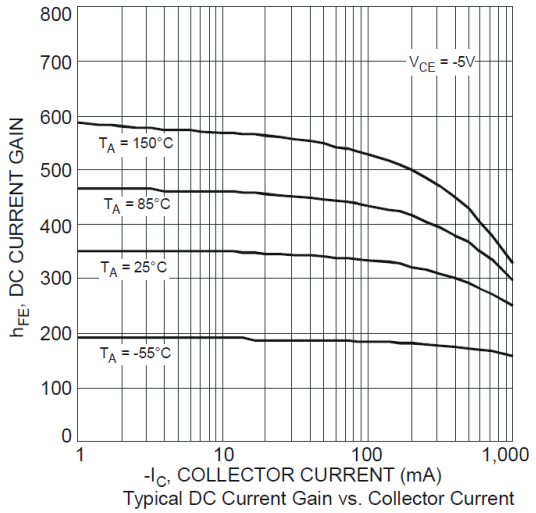
Pulse Power Dissipation

Electrical Characteristics – Q1 & Q2 (@T_A = +25°C, unless otherwise specified.)

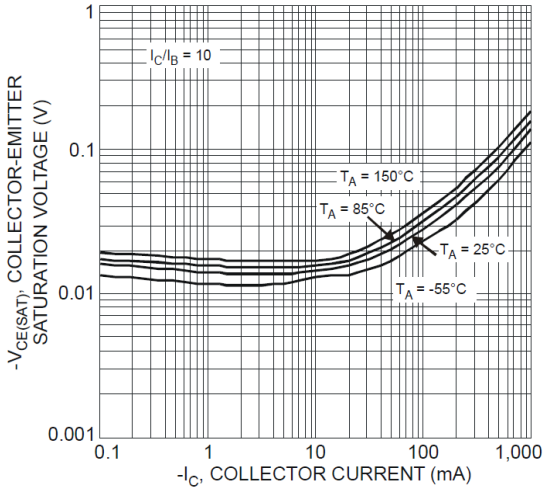
Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV_{CBO}	-60	—	—	V	I_C = -100µA
Collector-Emitter Breakdown Voltage (Note 11)	BV_{CEO}	-60	—	—	V	I_C = -10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	—	—	V	I_E = -100µA
Collector-Base Cutoff Current	I_{CBO}	—	—	-100	nA	V_{CB} = -48V, I_E = 0
		—	—	-50	µA	V_{CB} = -48V, I_E = 0, T_A = +150°C
Emitter-Base Cutoff Current	I_{EBO}	—	—	-100	nA	V_{EB} = -5.6V, I_C = 0
DC Current Gain (Note 11)	h_{FE}	170	—	—	—	V_{CE} = -2V, I_C = -100mA
		120	—	—		V_{CE} = -2V, I_C = -500mA
		70	—	—		V_{CE} = -2V, I_C = -1A
Collector-Emitter Saturation Voltage (Note 11)	$V_{CE(sat)}$	—	—	-180	mV	I_C = -500mA, I_B = -50mA
		—	—	-340		I_C = -1A, I_B = -100mA
		—	—	-550		I_C = -1A, I_B = -50mA
Equivalent On-Resistance (Note 11)	$R_{CE(sat)}$	—	—	360	mΩ	I_E = -0.5A, I_B = -50mA
Base-Emitter Saturation Voltage (Note 11)	$V_{BE(sat)}$	—	—	-1	V	I_C = -0.5A, I_B = -50mA
		—	—	-1.0		I_C = -1A, I_B = -50mA
		—	—	-1.1		I_C = -1A, I_B = -100mA
Base-Emitter Turn-on Voltage (Note 11)	$V_{BE(on)}$	—	—	-0.9	V	V_{CE} = -2V, I_C = -0.5A
Transition Frequency	f_T	65	—	—	MHz	V_{CE} = -10V, I_C = -50mA, f = 100MHz
Output Capacitance	C_{obo}	—	—	15	pF	V_{CB} = -10V, f = 1MHz
Turn-On Time	t_{on}	—	75	—	ns	V_{CC} = -10V, I_C = -0.5A, I_{B1} = -I_{B2} = 25mA
Delay Time	t_d	—	35	—	ns	
Rise Time	t_r	—	40	—	ns	
Turn-Off Time	t_{off}	—	265	—	ns	
Storage Time	t_s	—	230	—	ns	
Fall Time	t_f	—	35	—	ns	

Note: 11. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤2%.

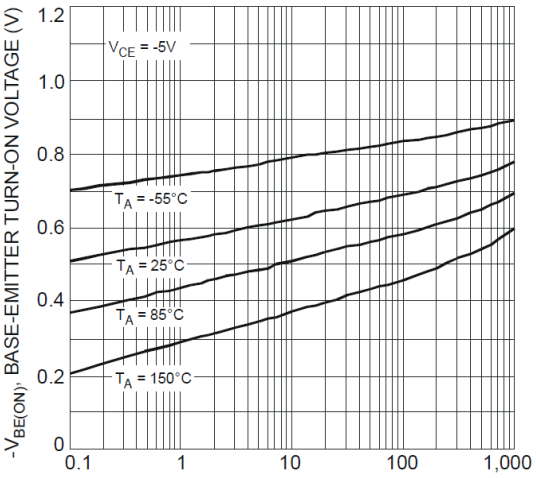
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



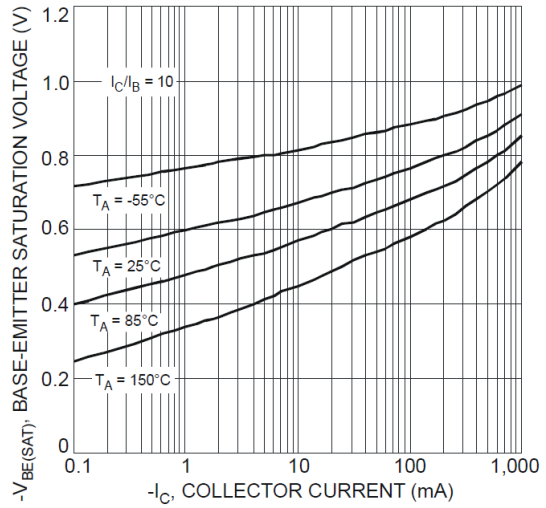
Typical DC Current Gain vs. Collector Current



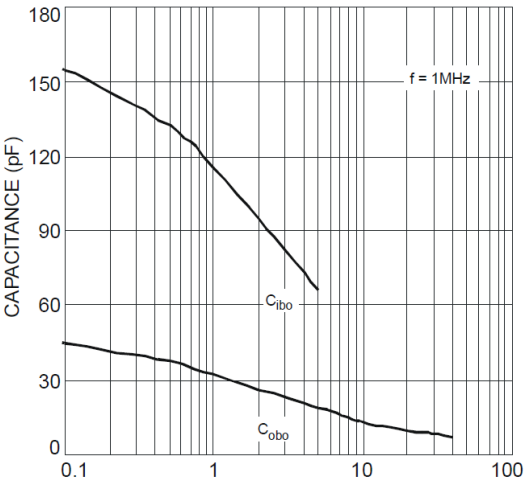
Typical Collector-Emitter Saturation Voltage vs. Collector Current



Typical Base-Emitter Turn-On Voltage vs. Collector Current



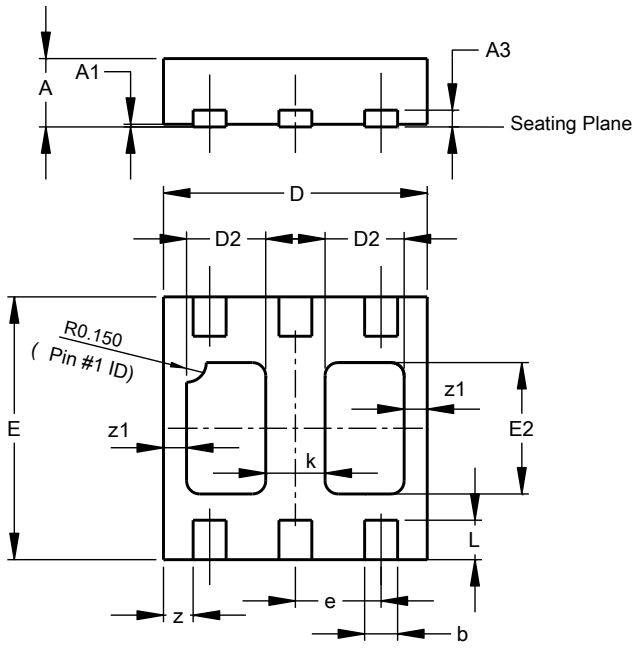
Typical Base-Emitter Saturation Voltage vs. Collector Current



Typical Capacitance Characteristics

Package Outline Dimensions

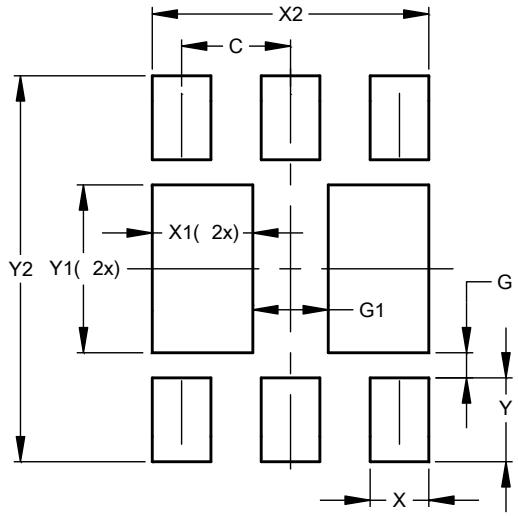
Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



U-DFN2020-6 Type B			
Dim	**Min**	**Max**	**Typ**
A	0.545	0.605	0.575
A1	0.00	0.05	0.02
A3	-	-	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
D2	0.50	0.70	0.60
e	-	-	0.65
E	1.95	2.075	2.00
E2	0.90	1.10	1.00
k	-	-	0.45
L	0.25	0.35	0.30
z	-	-	0.225
z1	-	-	0.175
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	0.650
G	0.150
G1	0.450
X	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300

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